

**BYC75W-1200P** 

## Hyperfast power diode

Rev.03 - 25 January 2021

**Product data sheet** 

### **1. General description**

EEPP<sup>™</sup> - Efficiency Enhanced Pt Planar rectifier in a TO247-2L plastic package.

### 2. Features and benefits

- Fast switching
- · Reduces switching losses with improved lower reverse recovery charge
- Soft recovery characteristics
- Low thermal resistance
- Low leakage current
- Planar termination structure
- High operating temperature capability (T<sub>j(max)</sub> = 175°C)
- Higher I<sub>FSM</sub> capability

### 3. Applications

- Switched-Mode Power Supplies
- Power factor correction diode
- Uninterrupted Power Supply

### 4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter Conditions			Values			Unit
Absolute	maximum rating						
$V_{\text{RRM}}$	repetitive peak reverse voltage		1200			V	
$I_{F(AV)}$	average forward current	$δ = 0.5$ ; square-wave pulse; $T_{mb} \le 75$ °C; Fig. 1; Fig. 2; Fig. 3	75			A	
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; t <sub>p</sub> = 25 µs; T <sub>mb</sub> ≤ 75 °C; square-wave pulse	150			А	
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	600			A	
		$t_{\rm p}$ = 8.3 ms; $T_{j(\text{init})}$ = 25 °C; sine-wave pulse		6	60		А
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 75 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	2.8	3.3	V
		I <sub>F</sub> = 75 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	2.2	-	V
Dynamic	characteristics				1		
t <sub>rr</sub>	reverse recovery time $I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{ d}_F/\text{d}t = 100 \text{ A}/\mu\text{s};$ $T_i = 25 \text{ °C}; \text{ Fig. 7}$			-	-	85	ns
Avalanch	ne energy						
E <sub>AS</sub>	non-repetitive avalanche energy	I <sub>R</sub> = 1.6 A; T <sub>j(init)</sub> = 25 °C; L = 40 mH		50	-	-	mJ

## **5. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode		
2	А	anode		K — A 001aaa020
mb	mb	mounting base; connected to cathod	<b>6</b> K A TO247-2L	

## 6. Ordering information

Table 3. Ordering information						
Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYC75W-1200P	TO247-2L	BYC75W-1200PQ	Tube	30	TO247A-2L	22-Jun-2017

## 7. Marking

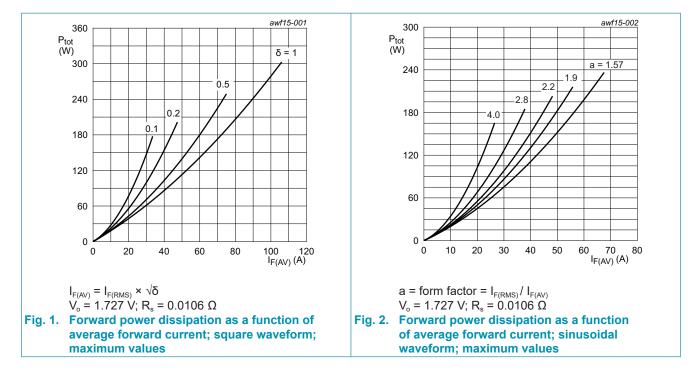
Table 4. Marking codes				
Type number	Marking codes			
BYC75W-1200P	BYC75W 1200P			

## 8. Limiting values

#### Table 5. Limiting values

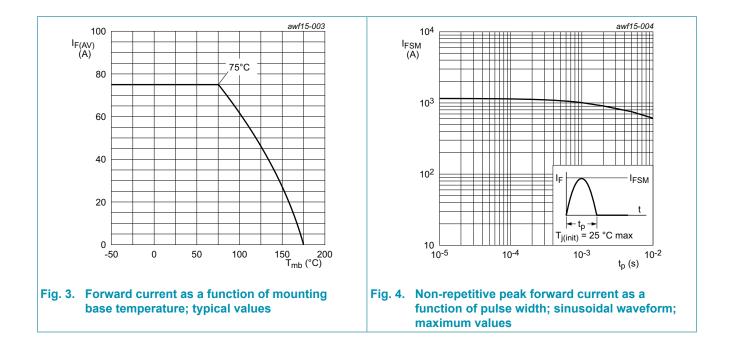
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{\text{RRM}}$	repetitive peak reverse voltage		1200	V
V <sub>RWM</sub>	crest working reverse voltage		1200	V
V <sub>R</sub>	reverse voltage	DC	1200	V
I <sub>F(AV)</sub>	average forward current	δ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 75 °C; Fig. 1; Fig. 2; Fig. 3	75	A
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 75 °C; square-wave pulse	150	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	600	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	660	A
T <sub>stg</sub>	storage temperature		-55 to 175	°C
Tj	junction temperature		-55 to 175	°C



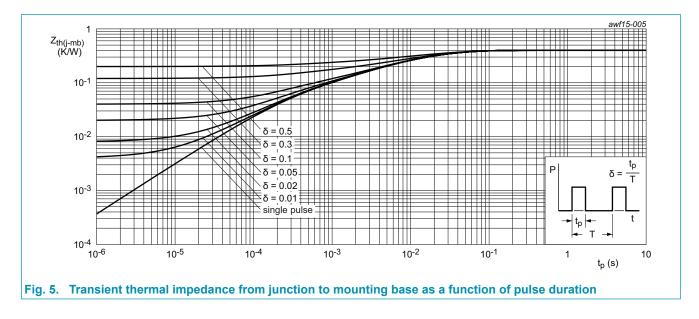
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## 9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	0.4	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	45	-	K/W

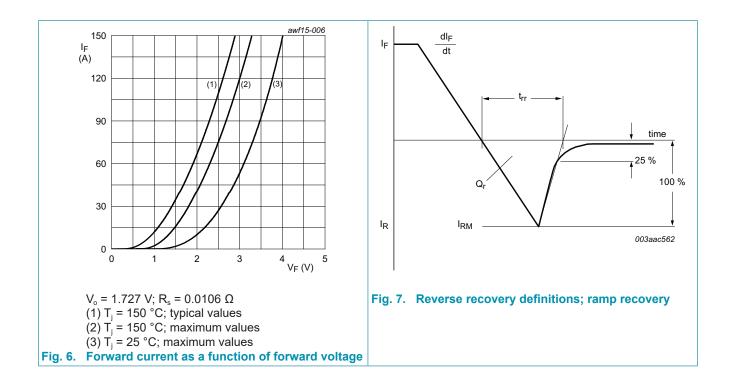


## **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 75 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	2.8	3.3	V
		I <sub>F</sub> = 75 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	2.2	-	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	-	250	μA
		V <sub>R</sub> = 600 V; T <sub>j</sub> = 125 °C	-	-	2	mA
Dynamic	characteristics	1				
Q <sub>r</sub>	reverse charge	$I_F = 50 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 25 ^\circ\text{C}; \text{ Fig. 7}$	-	1282	-	nC
		$I_F = 50 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	3729	-	nC
		$I_F = 50 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 150 \text{ °C}; Fig. 7$	-	4608	-	nC
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s};$ $T_j = 25 ^\circ\text{C}; \text{ Fig. 7}$	-	-	85	ns
		$I_F = 50 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 25 ^\circ\text{C}; \text{ Fig. 7}$	-	113	-	ns
		$I_F = 50 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; \frac{\text{Fig. 7}}{2}$	-	232	-	ns
		$I_F = 50 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 150 \text{ °C}; \frac{\text{Fig. 7}}{2}$	-	265	-	A
I <sub>RM</sub>	peak reverse recovery current	$I_F = 50 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 25 ^\circ\text{C}; \text{ Fig. 7}$	-	22.4	-	A
		$I_F = 50 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	32	-	A
		$I_F = 50 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 150 \text{ °C}; Fig. 7$	-	34.6	-	A
Avalanch	ne energy	·				
E <sub>AS</sub>	non-repetitive avalanche energy	I <sub>R</sub> = 1.6 A; T <sub>j(init)</sub> = 25 °C; L = 40 mH	50	-	-	mJ

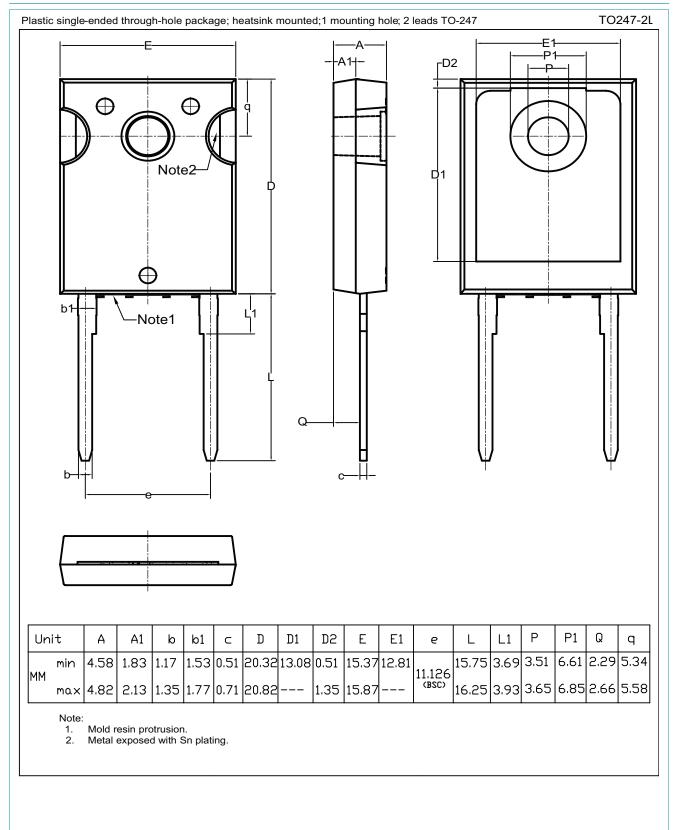
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#### BYC75W-1200P Hyperfast power diode

## 11. Package outline



## BYC75W-1200P

#### Hyperfast power diode

## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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